



Sierra Components, Inc.

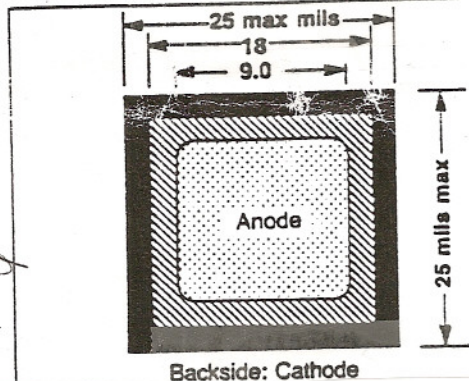
2222 Park Place Building 3 Suite E • Minden, Nevada 89423
 Phone: 775.783.4940 Fax: 775.783.4947

Chip back potential is the level which bulk silicon is maintained by on-chip connection, or it is the level to which the chip back must be connected when specifically stated below. If no potential is given the chip back should be isolated.

"A" Series, high level — tested at a 50 milliwatt dissipation level. *

ELECTRICAL CHARACTERISTICS $V_F = 1.5$ volts max @ $I_F = 200$ mA for all types, $T_A = 25$ °C unless otherwise noted.

Die Number (Note 1)	Nearest 1N Equivalent	Nominal Zener Voltage V_Z @ I_{ZT} Volts (Note 1)	Test Current I_{ZT} mA	Max Zener Impedance Z_{ZT} @ I_{ZT} Ohms	Max Reverse Leakage Current		
					I_R μA	@ V_R Volts	
						Tolerance	
						10%	5.0%
MZC2.4A10	1N5221, 1N4370	2.4	21	53	100	0.95	1.0
MZC2.5A10	1N5222	2.5	20	53	100	0.95	1.0
MZC2.7A10	1N5223, 1N4371	2.7	19	52	75	0.95	1.0
MZC2.8A10	1N5224	2.8	18	51	75	0.95	1.0
MZC3.0A10	1N5225, 1N4372	3.0	17	50	50	0.95	1.0
MZC3.3A10	1N5226, 1N746	> 3.3	15	47	25	0.95	1.0
MZC3.6A10	1N5227, 1N747	3.6	14	43	15	0.95	1.0
MZC3.9A10	1N5228, 1N748	3.9	13	35	10	0.95	1.0
MZC4.3A10	1N5229, 1N749	4.3	12	29	5.0	0.95	1.0
MZC4.7A10	1N5230, 1N750	4.7	11	24	5.0	1.9	2.0
MZC5.1A10	1N5231, 1N751	5.1	9.8	21	5.0	1.9	2.0
MZC5.6A10	1N5232, 1N752	5.6	8.9	25	5.0	2.9	3.0
MZC6.0A10	1N5233	6.0	8.3	30	5.0	3.3	3.5
MZC6.2A10	1N5234, 1N753	6.2	8.1	31	5.0	3.8	4.0
MZC6.8A10	1N5235, 1N754	6.8	7.3	38	3.0	4.8	5.0
MZC7.5A10	1N5236, 1N755	7.5	6.7	43	3.0	5.7	6.0
MZC8.2A10	1N5237, 1N756	8.2	6.1	49	3.0	6.2	6.5
MZC8.7A10	1N5238	8.7	5.7	52	3.0	6.2	6.5
MZC9.1A10	1N5239, 1N757	9.1	5.5	54	3.0	6.7	7.0
MZC10A10	1N5240, 1N758	10	5.0	60	3.0	7.6	8.0



METALLIZATION —
 Top Al
 Back Au
 GOLD THICKNESS 3000Å min
 DIE THICKNESS 8 ± 2 mils
 BONDING PAD SIZE —
 Anode 9.0 x 9.0 mils

Backside Potential:
 Mask Ref:

APPROVED BY:MG

DIE SIZE :25x25

DATE: 12/22/08

MFG:MOT

THICKNESS:

P/N:DZD200